IN THE SPECIFICATION:

Please amend page 15, last paragraph as follows:

The signal line 8 and the power supply line 9 are laid out with the AI wiring vertically at both right and left sides of the pixel 10. The signal line 8 and the power supply line 9 are disposed in parallel and formed by processing the same metallic wiring layer. The gate wiring 21 is laid out so as to be overlapped with part of the signal line 8, thereby the part of the signal line 8 comes to be used as the storage capacitor 4 as is. Part of the gate wiring 21 is overlapped with the polycrystalline silicon thin film island 22 connected to the power supply line 9 so as to form the driving TFT 2. The polycrystalline silicon thin film island 23 connected to the gate wiring 21 forms the reset switch 6 at an intersection point with a reset gate 11 formed with the gate wiring and the OLED switch 7 at an intersection point with an OLED gate 12 formed with the same gate wiring respectively. The other end of the OLED switch 7 is connected to a transparent electrode 25 through the contact hole 24 for the AI wiring and the transparent electrode. An organic EL element 1 provided with an organic illuminating layer and a common ground is provided on the transparent electrode 25. Those items are general ones, so that the description for them is omitted here.

Please amend page 20, last paragraph as follows:

Each pixel 30 is provided with an organic EL element 1 used as an electro-luminescent element. The cathode terminal of the organic EL element 1 is connected to a common ground. The anode terminal of the element 1 is connected to a power supply line 9 through an OLED switch 7 and a channel of a driving TFT 2. The gate of the driving TFT 2 is connected to the signal line 8 through the storage capacitor 34 and a reset switch 6 is provided between the drain terminal and the gate terminal of the driving TFT 2. Particularly, in this second embodiment, each of the driving TFT 2, the OLED switch 7, and the reset switch 6, as well as the storage capacitor 34 is formed with a p-type polycrystalline silicon TFT on a glass substrate. The storage capacitor 34 may be a MOS (Metal-Oxide-Semiconductor) capacitor that uses a p-channel. on a glass substrate. In this embodiment, the signal voltage applied to the signal line 8 is set so as to become lower than the resetting time voltage of the driving TFT (the voltage of the power supply line 9 - |Vth|). Consequently, a channel is always formed in the p-type polycrystalline silicon TFT used as the storage capacitor 34 so as to stabilize the gate capacitor.

Please amend page 29, last paragraph as follows:

Fig. 12 shows a circuit diagram of a pixel of the organic EL display panel in this fourth embodiment of the present invention. Each pixel 60 is provided with an organic EL element 61 used as an electro-luminescent element. The anode terminal of the organic EL element 61 is connected to a common ground and the cathode terminal of the element 61 is connected to a power supply line 9 through an OLED switch 67 and a channel of a driving TFT 62. And, the gate of the driving TFT 62 is connected to a signal line 8 through a storage capacitor 64 and a reset switch 66 is provided between the drain terminal and the gate terminal of the driving TFT 62. In this fourth embodiment, each of the driving TFT 62, the OLED switch 67, the reset

switch 66, and the storage capacitor 64 are formed specially with an n-type amorphous silicon TFT on a glass substrate. The storage capacitor 64 may be a MOS (Metal-Oxide-Transistor) capacitor that uses an n-channel. In that connection, the signal voltage applied to the signal line 8 is set so as to become lower than the resetting time voltage of the driving TFT 62 (the voltage of the power supply line 9 + |Vth|). Consequently, a channel is always formed at the n-type amorphous silicon TFT used as the storage capacitor 64, thereby the gate capacitor is usable as a stable capacitor.